



Substitute for Form 1449 A & B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	10/580,560
		Confirmation Number	Not yet assigned
		Filing Date	May 26, 2006
		First Named Inventor	Koji KUDO
		Art Unit	Not yet assigned
		Examiner Name	Not yet assigned
Sheet	1	of	1
		Attorney Docket Number	Q95169

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
/X.N./		US 4,740,987	A	04-26-1988	McCall, Jr. et al.
/X.N./		US 4,796,273	A	01-03-1989	Yamaguchi
/X.N./		US 2003/0021319	A1	01-30-2003	Aoki
/X.N./		US 2002/0159705	A1	10-31-2002	Naniwae

FOREIGN PATENT DOCUMENTS							
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/X.N./		JP	63-80590	A	04-11-1988		
/X.N./		JP	3-283483	A	12-13-1991		
/X.N./		JP	62-112391	A	05-23-1987		
/X.N./		JP	2002-198611	A	07-12-2002		
/X.N./		JP	63-62390	A	03-18-1988		
/X.N./		JP	8-186334	A	07-16-1996		
/X.N./		JP	2624140	B2	04-11-1997		
/X.N./		JP	2003-46190	A	02-14-2003		
/X.N./		JP	2545994	B2	08-08-1996		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
/X.N./		M. Aoki et al., "85°C - 10Gbit/s Operation of 1.3-μm InGaAlAs MQW-DFB Laser", ECOC2000 Vol. 1, pp. 123-124.	
/X.N./		K. Nakahara et al., "115°C, 12.5-Gb/s Direct Modulation of 1.3-μm InGaAlAs-MQW RWG DFB Laser with Notch-Free Grating Structure for Datacom Applications", OFC2003 PDP40.	
/X.N./		G. Shtengel et al., "High-speed Vertical-Cavity Surface Emitting Laser", IEEE Photonic Technology Letters, 1993, vol. 5, no. 12, pp. 1359-1362.	
/X.N./		A. Ramakrishnan et al., "Electrically Pumped 10 Gbit/s MOVPE-Grown Monolithic 1.3 μm VCSEL with GaInNAs Active Region", IEE Electronics Letters, 2002, Vol. 38, No. 7.	
/X.N./		M. Uchida et al., "An AlGaAs Laser with High-Quality Dry Etched Mirrors Fabricated Using an Ultrahigh Vacuum in Situ Dry Etching and Deposition Processing System", IEEE Journal of Quantum Electronics, 1998, vol. 24, no. 11, pp. 2170-2176.	
/X.N./		Y. Itaya et al., "Low Threshold Current GaInAsP/InP DFB Lasers", IEEE Journal of Quantum Electronics, Vol. QE-23, No. 6, June 1987, pp. 828-834.	
/X.N./		T. Aoyagi et al., "Recent Progress of 10Gb/s Laser Diodes for Metropolitan Area Networks", SPIE, 2001, vol. 4580, APOC 2001, Beijing, China.	
/X.N./		T. Yuasa et al., "Performance of Dry-Etched Short Cavity GaAs/AlGaAs Multi-quantum-Well Lasers", Journal of Applied Physics, 1998, vol. 63, no. 5, pp. 1321-1327.	

Examiner Signature	/Xinning Niu/	Date Considered	12/05/2007
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